

Read / Write amplifier for FDD

BH6629BFS

The BH6629BFS, a read / write IC designed for floppy disk drives, has a recording system that puts top priority on saddle margin. Offers multi-step switching of write current, while density and inner track / outer track edge are switched internally.

●Applications

Floppy disk drives (1MB and 2MB drives)

●Features

- 1) Internal active filter switch.
- 2) Time domain filter (with internal switching based on transfer rate).
- 3) Internal switching of write current density and inner track / outer track.

●Absolute maximum ratings (unless otherwise noted, Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|-----------------------|--------|--------------|------|
| Power supply voltage | Vcc | +7 | V |
| Operating temperature | Topr | 0~+70 | °C |
| Storage temperature | Tstg | -55~+125 | °C |
| Digital input voltage | VI | -0.5~Vcc+0.3 | V |
| RW pin voltage | VRW | +15 | V |
| LVS output voltage | VLVS | Vcc+0.3 | V |
| ED pin voltage | VER | Vcc+0.3 | V |
| Power dissipation | Pd | 650* | mW |

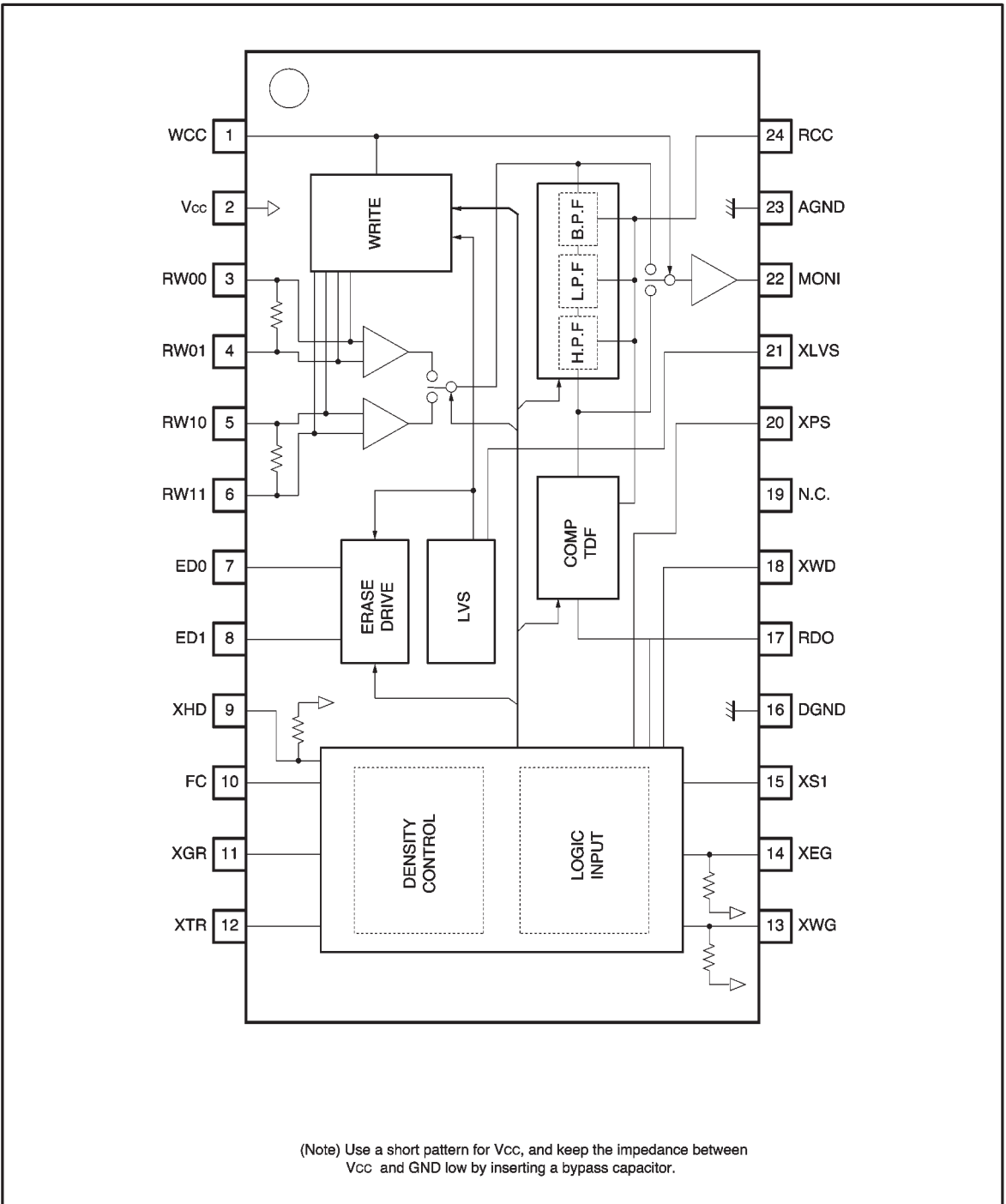
* Reduced by 6.5mW for each increase in Ta of 1°C over 25°C.

●Recommended operating conditions (Ta = 25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|----------------------|--------|------|------|------|------|
| Power supply voltage | Vcc | 4.5 | 5.0 | 5.5 | V |



● Block diagram


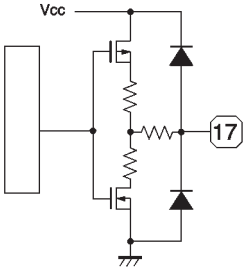
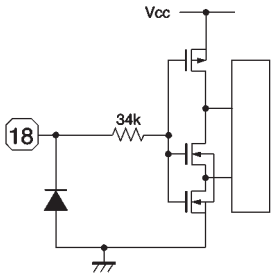


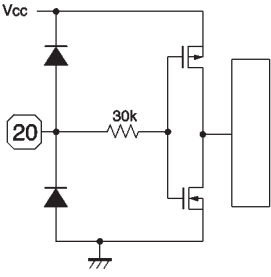


(Note) Use a short pattern for Vcc, and keep the impedance between Vcc and GND low by inserting a bypass capacitor.

● Pin descriptions

| Pin No. | Pin name | Equivalent circuit | Function |
|---------|----------|--------------------|--|
| 1 | WCC | | <p>For connecting the write current adjustment resistor</p> <p>Connect the write current adjustment resistor between this pin and Vcc</p> <p>Setting this pin to the low level during reading switches MONI to differentiator output</p> |
| 2 | Vcc | | Power supply pin |
| 3 | RW00 | | <p>Active when SIDE0 and the read/write head connecting pin (pin 15, XS1) is at the high level (side 0)</p> <p>Starts at RW00 during the start of writing (from reading to writing)</p> |
| 4 | RW01 | | |
| 5 | RW10 | | <p>Active when the read / write head connecting pin (pin 15, XS1) is at the low level (side 1)</p> <p>Starts at RW10 during the start of writing (from reading to writing)</p> |
| 6 | RW11 | | |
| 7 | ED0 | | Side 1 erase current sink |
| 8 | ED1 | | Side 1 erase current sink |

| Pin No. | Pin name | Equivalent circuit | Function |
|---------|----------|--------------------|--|
| 9 | XHD | | <p>1 MB/2 MB selector High=1MB Low=2MB</p> |
| 10 | FC | | <p>Option 2 selector Selector signal high level = active</p> |
| 11 | XGR | | <p>Option mode selector Controls the write current</p> |
| 12 | XTR | | <p>Inner edge/outer edge position setting Controls the filter and write current</p> |
| 13 | XWG | | <p>Write enable gate (Schmidt input) Low = active</p> |
| 14 | XEG | | <p>Erase enable gate (Schmidt input) Low = active</p> |
| 15 | XS1 | | <p>Head/side switching signal Low = active (Schmidt input) High = side 0, low = side 1</p> |

| Pin No. | Pin name | Equivalent circuit | Function |
|---------|----------|---|--|
| 16 | DGND |  | Digital ground |
| 17 | RDO |  | Read data output TTL high level = active |
| 18 | XWD |  | Write data input Operates at falling edge (Schmidt input) |
| 19 | N.C. |  |  |
| 20 | XPS |  | Power save selector Low = active |

| Pin No. | Pin name | Equivalent circuit | Function |
|---------|----------|--------------------|---|
| 21 | XLVS | | <p>External low level-voltage detection pin Open collector output when low level voltage is detected Switches to low level when Vcc drops below the specified voltage</p> |
| 22 | MONI | | <p>Preamplifier output and differentiator output monitoring Monitor is switched with pin 1 (WCC)</p> |
| 23 | AGND | | <p>Analog ground</p> |
| 24 | RCC | | <p>Filter (LPF, BPF) cutoff frequency and TDF first M/M pulse width setting resistor connection</p> |

● Electrical characteristics (unless otherwise noted, Ta = 25°C, V_{CC} = 5V)

Supply current

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|------------------------------|--------|------|------|------|------|------------|
| Current dissipation, Standby | ICCST | — | 190 | 400 | μA | *1 |
| Current dissipation, Read | ICCR | — | 28 | 40 | mA | *1 |
| Current dissipation, Write | ICCW | — | 8.5 | 15 | mA | *2 |

*1 RRCC=2.0 [kΩ] (XHD=H)

*2 RWCC=2.4 [kΩ] (When 2MB inner track, XGR = "H", except IWR and IER)

Low level voltage detection circuit

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------|--------|------|------|------|------|--|
| Threshold voltage 1 | VTH1+ | — | 4.05 | 4.3 | V | When power supply voltage rises, internal LVS/ write protect |
| | VTH1- | 3.6 | 3.85 | 4.1 | V | When power supply voltage falls, internal LVS/ write protect |
| Threshold voltage 2 | VTH2+ | — | 3.92 | 4.17 | V | When supply voltage rises, external LVS |
| | VTH2- | 3.47 | 3.72 | 3.97 | V | When supply voltage falls, external LVS |
| Hysteresis voltage | VH | 50 | — | — | mV | |
| Output low level voltage | VOL | — | — | 0.40 | V | V _{CC} =2.5[V] IOL=0.2[mA] |
| Output leakage current | IOH | — | — | 10 | μA | |

Recovery time

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-----------------|--------|------|------|------|------|------------|
| POWER·SAVE→READ | TR2 | — | — | 500 | μs | by XPS |
| READ→ERASE | TR3 | — | — | 6 | μs | by XEG |
| READ→WRITE | TR4 | — | — | 4 | μs | by XWG |
| WRITE→READ | TR5E | — | — | 20 | μs | by XEG |
| | TR5W | — | — | 160 | μs | by XWG |
| SIDE0↔SIDE1 | TR6 | — | — | 40 | μs | by XS1 |
| 1MB↔2MB | TR7 | — | — | 40 | μs | by XHD |

Preamplifier

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|--------|------|------|------|-------------------|--|
| Voltage gain (1) | GVD1 | 43 | 46 | 49 | dB | f=125[kHz], VIN=2.5[mV _{P-P}](differential) (OPTION outer edge) |
| Voltage gain (2) | GVD2 | 46 | 49 | 52 | dB | f=125[kHz], VIN=2.5[mV _{P-P}](differential) (1 MB/2 MB outer edge, OPTION inner edge) |
| Voltage gain (3) | GVD3 | 49 | 52 | 56 | dB | f=125[kHz], VIN=1.5[mV _{P-P}](differential) (1 MB/2 MB inner edge) |
| SIDE0↔SIDE1 crosstalk | GCTLK | 50 | — | — | dB | f=125[kHz], VIN=100[mV _{P-P}] (differential)*3 |
| Differential input resistance | RID | — | 4 | — | kΩ | 8.0 kΩ input resistance parallel 8.0 kΩ damping resistance |
| Input conversion noise voltage | VN | — | 2.5 | 3.7 | μV _{rms} | f=500[Hz]~1[MHz] |
| Input sink current | ISINK | — | 180 | — | μA | |
| Differential input voltage amplitude (1) | VIN | — | — | 5.0 | mV _{P-P} | 5% distortion (sine wave input) (OPTION outer edge) |
| Differential input voltage amplitude (2) | VIN | — | — | 3.5 | mV _{P-P} | 5% distortion (sine wave input) (1 MB/2 MB outer edge, OPTION inner edge) |
| Differential input voltage amplitude (3) | VIN | — | — | 2.0 | mV _{P-P} | 5% distortion (sine wave input) (1 MB/2 MB, inner edge) |
| Common mode rejection ratio | CMRR | 50 | — | — | dB | f=125[kHz], VIN=100[mV _{P-P}]*3 |
| Supply voltage ratio rejection | PSRR | 40 | — | — | dB | f=250[kHz], VIN=100[mV _{P-P}]*3 |

Preamplifier/L.P.F/differentiator (B.P.F)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--|----------------|------|------|------|------|--|
| Filter time constant accuracy | EFIL | -10 | — | +10 | % | *3 |
| Total gain (preamplifier/ LPF/differentiator) (1) | GVDD1 | 43.0 | 47.0 | 51.0 | dB | f=250[kHz], VIN=2.5[mV _{P-P}](differential) (2 MB outer edge) |
| Total gain (preamplifier/ LPF/differentiator) (2) | GVDD2 | 44.0 | 48.0 | 52.0 | dB | f=250[kHz], VIN=2.5[mV _{P-P}](differential) (2 MB inner edge) |
| Total gain (preamplifier/ LPF/differentiator) (3) | GVDD3 | 40.5 | 44.5 | 48.5 | dB | f=250[kHz], VIN=2.5[mV _{P-P}](differential) (OPTION 2 outer edge) |
| Differentiator output peaking frequency setting range | f ₀ | 0.1 | — | 0.5 | MHz | Defined according to typical value in the settings |

*3 RRCC=2.0 [kΩ] (XHD=L, XTR=H, FC=L)

Comparator and waveform shaping

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|----------------------------------|--------|------|------|------|------|--|
| TDF M/M pulse width accuracy (1) | TDF1 | -10 | - | +10 | % | 1MB (Typ. : 2545[ns]) f=62.5[kHz]~125[kHz] *4 |
| TDF M/M pulse width accuracy (2) | TDF2 | -10 | - | +10 | % | 2MB, OPTION (Typ. : 1280[ns]) f=125[kHz]~250[kHz] *4 |
| RD pulse width | TRD | 270 | 400 | 530 | ns | Determination level: 1.5[V] |
| Rise time | TTLH | - | - | 70 | ns | Rise time between 0.4[V] and 2.0[V] |
| Fall time | TTHL | - | - | 70 | ns | Fall time between 2.0[V] and 0.4[V] |
| Peak shift | P. S. | - | - | 1.0 | % | f=250[kHz] , VIN=1[mV _{P-P}] (differ.) |
| Output low level voltage | VOL | - | - | 0.5 | V | |
| Output high level voltage | VOH | 2.7 | - | - | V | Level after 70 ns rise from 0.4 V |

*4 RRCC=2.0 [kΩ]

Write circuit

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|--------|------------------------|------|------|-------|----------------------------|
| Write current adjustment | IWR | 2.0 | - | 20 | mA0-P | |
| Write current accuracy | ACIW | -7.0 | - | +7.0 | % | *5 |
| Write current pairability | ΔIWR | -1.0 | - | +1.0 | % | RWCC=2.4[kΩ] |
| Write current power supply voltage dependency | PSIW | -4.0 | -0.8 | +3.0 | % / V | RWCC=2.4[kΩ] |
| Output saturation voltage | VSATRW | - | 0.4 | 1.0 | V | IWR=12[mA] |
| Off-state leakage current | ILKRW1 | - | - | 20 | μA | Unselected side |
| | ILKRW2 | - | - | 50 | μA | Selected side |
| Minimum write data pulse width | TWD | 70 | - | - | ns | |
| Write current switching ratio accuracy | ACIWTR | ±10× (1-setting ratio) | | | % | *6 |
| Damping resistance accuracy | ACDR | -25 | - | +25 | % | Write (typically 8.0 [kΩ]) |

*5 RWCC = 2.4[kΩ], adapted for desired setting of XTR1/XTR2

*6 Error in setting ratio (reference: 1 MB outer edge)

Erase output

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-----------------------------|--------|------|------|------|------|------------------------------|
| Erase current setting range | IER | - | - | 40 | mA | |
| Output saturation voltage | VSATER | - | 0.2 | 0.6 | V | IER=40[mA] |
| Output leakage current | IOH | - | - | 10 | μA | Off, ED0=ED1=V _{cc} |

Logic input

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------|--------|------|------|------|---------|---|
| Input high level voltage | VIH | 2.0 | — | — | V | |
| Input low level voltage | VIL | — | — | 0.8 | V | |
| Input voltage hysteresis | VH | 0.15 | — | — | V | Applies to XWD, XWG, XEG, XS1 |
| Input low level current | IIL1 | — | 50 | 100 | μ A | V _{CC} =5[V] VIL=GND Applies to XWG, XEG, XHD |

● Mode table

| Mode | | 1MB | | 2MB | | OPTION1 | | OPTION2 | | |
|-------------------------------|---------------|----------------------|---------------|---------------|---------------|-------------|---------------|---------------|-------------|--|
| Transfer rate | | 250[kbps] | | 500[kbps] | | 500[kbps] | | 500[kbps] | | |
| Input | Mode | XHD | HIGH | | LOW | | HIGH | | NO CARE | |
| | | FC | LOW | | LOW | | LOW | | HIGH | |
| | XGR | HIGH | | NO CARE | | LOW | | | | |
| track | XTR (XSWF) | Outer track | Inner track | Outer track | Inner track | Outer track | Inner track | Outer track | Inner track | |
| | | LOW | HIGH | LOW | HIGH | LOW | HIGH | LOW | HIGH | |
| Preamplifier gain [dB] | | 49 | 52 | 49 | 52 | 46 | 49 | 46 | 49 | |
| Output | Filter | f ₀ [kHz] | 187 | 224 | 372 | 376 | 350 | 372 | 350 | |
| | | Charac.(Q)*1 | C | D | D | A | C | D | C | |
| TDF | [nSEC] | 2545 | | 1280 | | 1280 | | | | |
| Write current switching ratio | | WCC | WCC ×0.733 | WCC ×0.433 | WCC ×0.318 | WCC | WCC ×0.733 | WCC ×0.733 | | |

*1 (A) Butterworth characteristics (C) Option characteristics

(However, RRCC=2.0 [k Ω])

(D) Refer to low-Q Butterworth characteristics, filter characteristics

Total filter peak frequency setting

$$f_0 = a / (RRCC [k\Omega + 0.09]) [kHz]$$

- a = 391 1M outer track
 468 1M inner track
 777 2M outer track
 786 2M inner track
 732 outer track (with OPTION 1), OPTION 2
 777 inner track (with OPTION 1)

TDF time constant setting

$$250 [kbps] : T = 939 \times RRCC [k\Omega] + 667 [ns]$$

$$500 [kbps] : T = 403 \times RRCC [k\Omega] + 474 [ns]$$

Write current setting

$$I_{wr} = \frac{24.0}{RWCC [k\Omega]} [mA]$$

● Filter characteristic

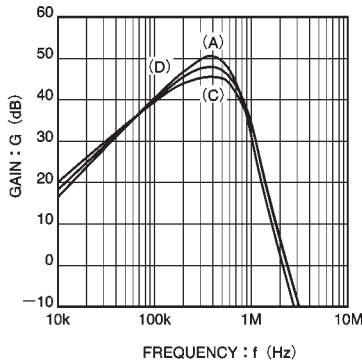
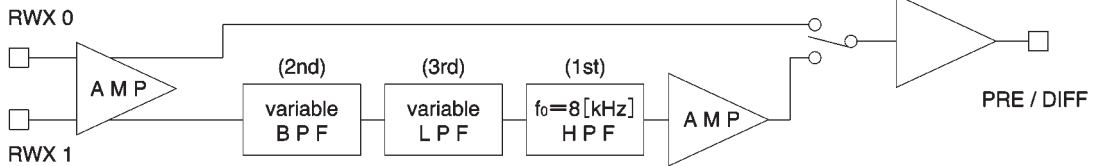
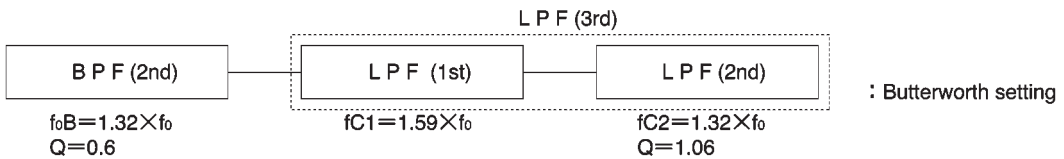


Fig. 1 PRE IN vs. DIFF OUT

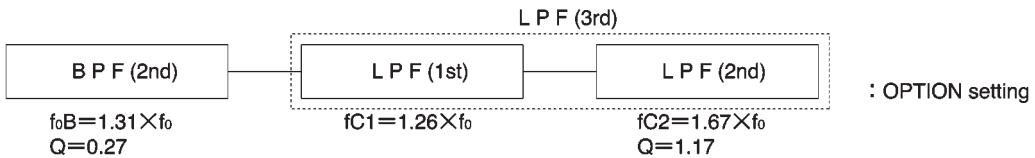
Preamplifier — differentiator(B.P.F)— L.P.F



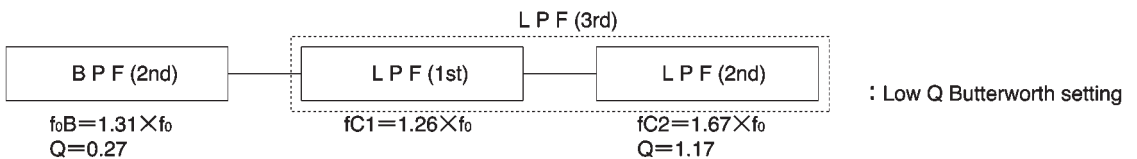
(A) Total characteristic peak frequency (f_0): 1MB, 2MB inner edge,



(C) Total characteristic peak frequency (f_0): OPTION1 outer edge, OPTION2



(D) Total characteristic peak frequency (f_0): 1MB, 2MB outer edge, OPTION1 inner edge



● Measurement circuit

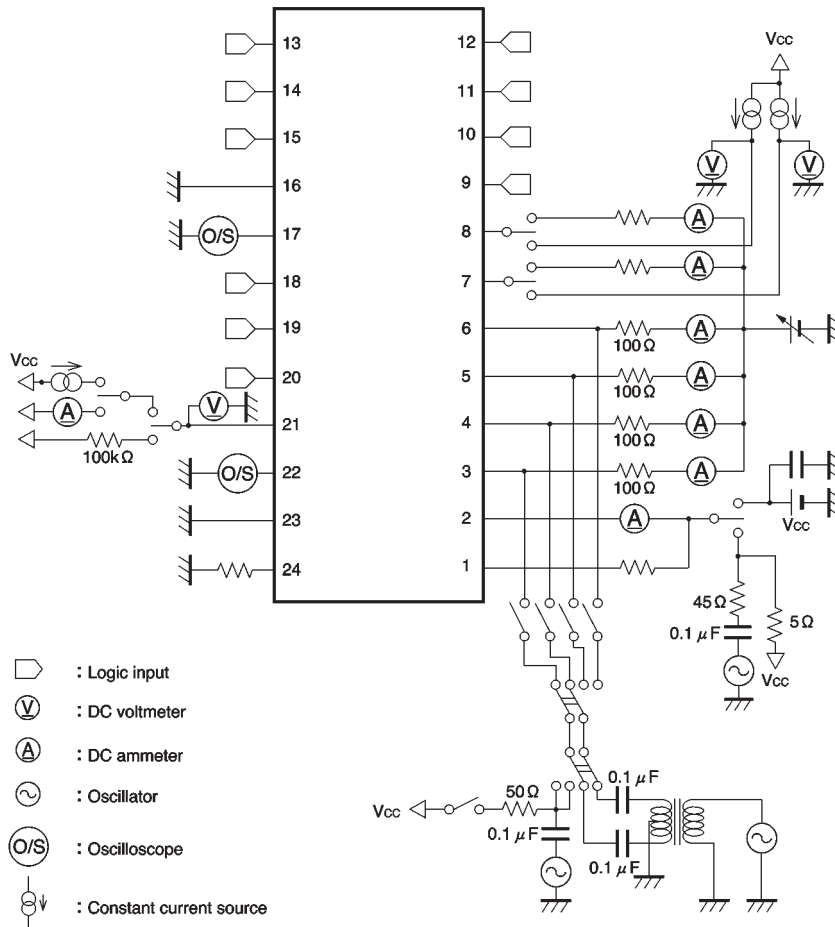


Fig. 2

● Circuit operation

(1) Read

The input signal from the head coils from each side of the disc is amplified by the preamplifier and then differentiated. The filter time constant can be set externally. After differentiation, the differential output is input to the comparator. The time domain filter detects zero cross, and the output is converted to read data. The monostable multivibrator width can be set externally, while the read data pulse width is a constant 400ns.

(2) Write

Input write data are converted to toggle movements by

the internal flip-flops, operating the write driver. The write driver current is supplied by the write current generator, but the externally set current can be controlled according to density and by selecting inner track/outer track.

(3) Erase

An open collector output pin is used, and the erase current is set with a resistor between it and the head.

(4) Power supply

When the low level voltage detector detects a drop in the supply voltage, writing and erasing are prohibited.

● Operation notes

- (1) Use a short pattern for V_{CC} , and a sufficiently wide AGND and DGND. Keep the impedance between V_{CC} and GND low by inserting a bypass capacitor.
- (2) Use a pattern that will minimize interference between digital signals and the head.

● Electrical characteristic curves

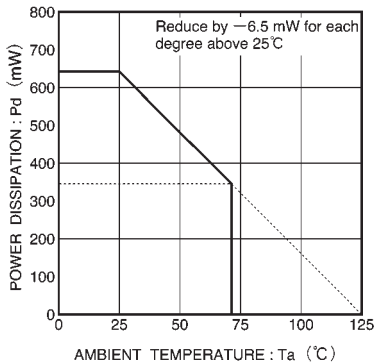


Fig. 3 Thermal derating curve

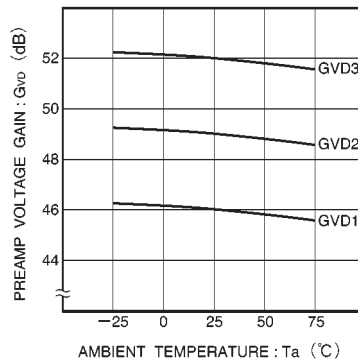


Fig. 4 Preamp voltage gain vs. ambient temperature.

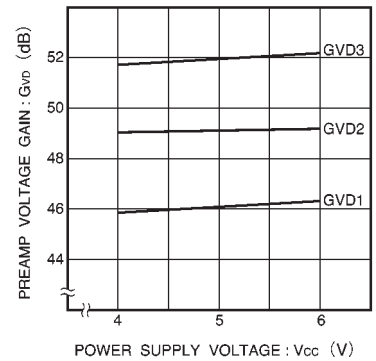


Fig. 5 Preamp voltage gain vs. power supply voltage

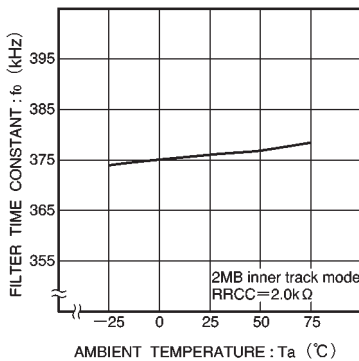


Fig. 6 Filter time constant (f_0) vs. ambient temperature

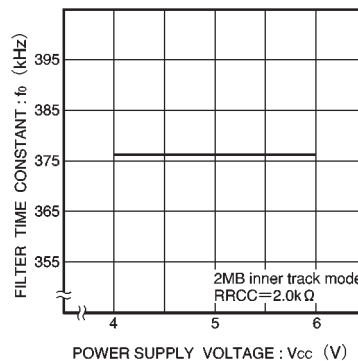


Fig. 7 Filter time constant vs. power supply voltage

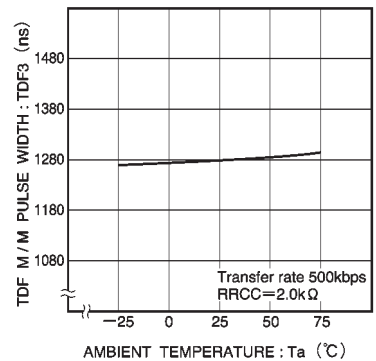


Fig. 8 TDF time constant vs. ambient temperature

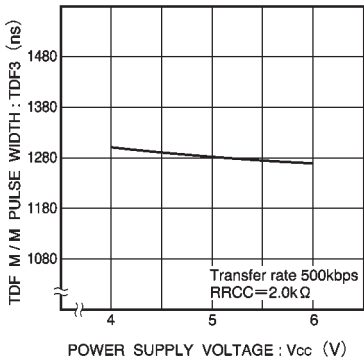


Fig. 9 TDF time constant vs. power supply voltage

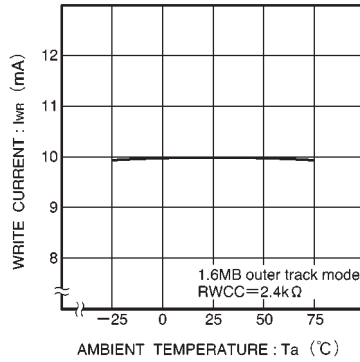


Fig. 10 Write current vs. ambient temperature

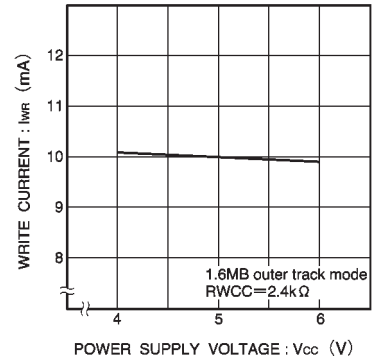


Fig. 11 Write current vs. power supply voltage

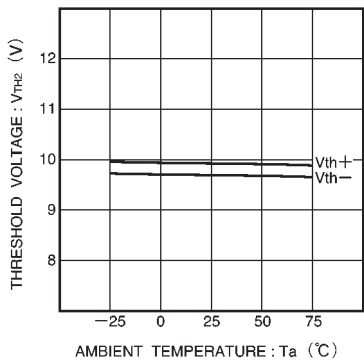


Fig. 12 Low level voltage detection voltage vs. ambient temperature

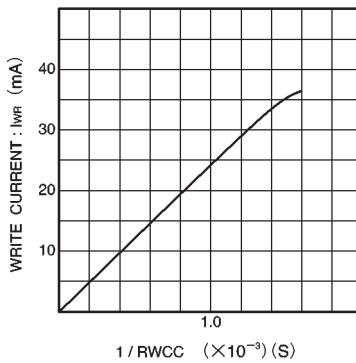


Fig. 13 Write current vs. write current adjustment resistance

● External dimensions (Units: mm)

